

(43) International Publication Date
08 May 2025 (08.05.2025)



(10) International Publication Number
WO 2025/096316 A1

(51) International Patent Classification:

<i>G01N 21/33</i> (2006.01)	<i>G01N 21/93</i> (2006.01)
<i>G01N 21/47</i> (2006.01)	<i>H01L 21/66</i> (2006.01)
<i>G01N 21/95</i> (2006.01)	

(21) International Application Number:

PCT/US2024/053159

(22) International Filing Date:

28 October 2024 (28.10.2024)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

63/546,758	01 November 2023 (01.11.2023)	US
18/756,439	27 June 2024 (27.06.2024)	US

(71) Applicant: **KLA CORPORATION** [US/US]; One Technology Drive, Milpitas, California 95035 (US).

(72) **Inventors:** **JENSEN, Earl**; 625 Barto Street, Santa Clara, California 95051 (US). **GUBLER, Joshua**; 5752 Ribchester Ct. San Jose, California 95123 (US).

(74) **Agent:** MCANDREWS, Kevin et al.; One Technology Drive, Milpitas, California 95035 (US).

(81) Designated States (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MU, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE,

(54) Title: METROLOGY METHOD OF CALIBRATING AND MONITORING RADIATION IN EUV LITHOGRAPHIC SYSTEMS

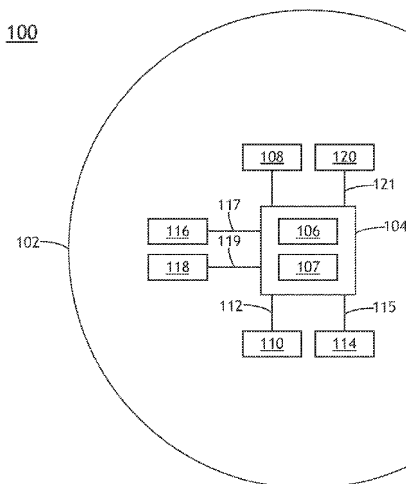


FIG. 1A

(57) Abstract: An instrumented substrate may provide a metrology platform for monitoring extreme ultraviolet (EUV) radiation in an image plane of a EUV lithography tool. The instrumented substrate may include in-band dosage sensors. The in-band dosage sensors may generate dosage measurements corresponding to the illumination which is in-band. The instrumented substrate may also include out-of-band dosage sensors and in-band scattered dosage sensors. The instrumented substrate may be housed within a front opening unified pod (FOUP) of a system.

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SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN,
GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*